

Notice of References Cited	Application/Control No. 09/818,193		Applicant(s)/Patent Under Reexamination CHUNG ET AL.	
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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,221,700	04-2001	Okuno et al.	438/151
*	B	US-6,767,843	07-2004	Lipkin et al.	438/758
*	C	US-2004/0101625	05-2004	Das et al.	427/378
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Li, Hui-Feng, et al, "Analysis of Fowler-Nordheim Injection in NO Nitrided Gate Oxide Grown on n-type 4H-SiC", Proc. 22 nd Int'l Conf. on Microelectronics (MIEL 2000) Vol.1, Nis Serbia, 5/14-17/2000, pp.331-333
	V	Chung, G.Y., et al, "Improved Inversion Channel Mobility for 4H-SiC MOSFETs Following High Temperature Anneals in Nitric Oxide", IEEE Electron Device Letters, Vol.22, No.4, 4/2001, pp.176-178
	W	Li, Hui-Feng, "Distribution and Chemical Bonding of N at NO Nitrided SiC/SiO ₂ Interface", IEEE 1999 pp.164-166
	X	Dimitrijević, S. et al, "Nitridation of Silicon-Dioxide Films Grown on 6H Silicon Carbide", IEEE Electron Device Letters, Vol.18, No. 5, 5/1977, pp.175-177

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

Notice of References Cited	Application/Control No. 09/818,193	Applicant(s)/Patent Under Reexamination CHUNG ET AL.	
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U.S. PATENT DOCUMENTS

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	A	US-			
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
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	J	US-			
	K	US-			
	L	US-			
	M	US-			

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	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Williams, J.R. et al, "Passivation of the 4H-SiC/SiO ₂ Interface with Nitric Oxide", Materials Science Forum, Vol.389-393 (2002), pp.967-972
	V	Chung, G.Y., et al, "Effect of Nitric Oxide Annealing on the Interface Trap.... Silicon Carbide", App. Phys. Lett., Vol.76, No.13, pp.1713-1715
	W	Des, M.K., "High Mobility 4H-SiC Inversion Mode MOSFETs Using Thermally Grown, NO annealed SiO₂, 56th Device Research Conf. 6/19-21/2000, Denver Co.
	X	Li, H.F., et al, "Electrical Characteristics of NO Nitrided SiO ₂ Grown on p-type 4H-SiC", Proc. 21 st Intl. Conf. on Microelectronics (MIEL '97) Yugoslavia, 14-1 September 1997, pp.611-612

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Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

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U.S. PATENT DOCUMENTS

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	A	US-			
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	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Jarnet, P., et al, "Physical Properties of N2O and NO-Nitrided Gate Oxides Grown on 4H-SiC", Appl. Phys. Lett. vol.79, No.3, 7/16/2001, pp.323-325
	V	Li, Hui-feng, et al, "Interfacial Characteristics of N2O and NO Nitrided SiO2 Grown on SiC by Rapid Thermal Processing", Appl. Phys. Lett, 70(15) 14 April 1997
	W	Lu, Chao Yang, et al., "Effect of Process Variations and Ambient Temperature on Electron Mobility at the SiO2/4H Si-C Interface", IEEE
		Transactions on Electron Devices, Vol. 50, No.7, July 2003, pp. 1582-1588

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.